

## N-Channel Enhancement Mode Power MOSFET

### Features

- $V_{DS} = 30V$ ,  $I_D = 18A$   
 $R_{DS(ON)} < 4\text{ m}\Omega$  @  $V_{GS} = 10V$   
 $R_{DS(ON)} < 7\text{ m}\Omega$  @  $V_{GS} = 4.5V$

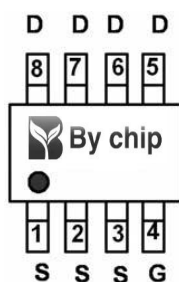
### General Features

- Advanced Trench Technology
- Provide Excellent  $R_{DS(ON)}$  and Low Gate Charge
- Lead Free and Green Available

100% UIS TESTED!  
100%  $\Delta V_{ds}$  TESTED!



SOP-8



pin assignment



Schematic diagram

### Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ , unless otherwise noted

| Parameter                                        | Symbol         | Value      | Unit             |
|--------------------------------------------------|----------------|------------|------------------|
| Drain-Source Voltage                             | $V_{DS}$       | 30         | V                |
| Continuous Drain Current                         | $I_D$          | 18         | A                |
| Pulsed Drain Current (note1)                     | $I_{DM}$       | 72         | A                |
| Gate-Source Voltage                              | $V_{GS}$       | $\pm 20$   | V                |
| Power Dissipation                                | $P_D$          | 2.1        | W                |
| Single pulse avalanche energy (note2)            | $E_{AS}$       | 64         | mJ               |
| Operating Junction and Storage Temperature Range | $T_J, T_{stg}$ | -55 To 150 | $^\circ\text{C}$ |

### Thermal Resistance

| Parameter                               | Symbol     | Value | Unit               |
|-----------------------------------------|------------|-------|--------------------|
| Thermal Resistance, Junction-to-Ambient | $R_{thJA}$ | 59    | $^\circ\text{C/W}$ |

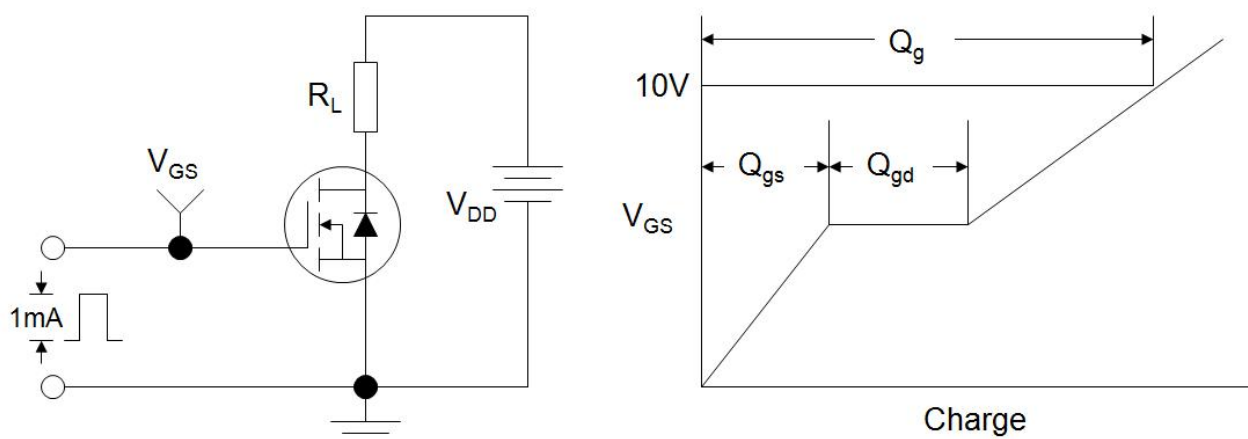
**Specifications**  $T_J = 25^{\circ}\text{C}$ , unless otherwise noted

| Parameter                               | Symbol               | Test Conditions                                                          | Value |      |      | Unit |
|-----------------------------------------|----------------------|--------------------------------------------------------------------------|-------|------|------|------|
|                                         |                      |                                                                          | Min.  | Typ. | Max. |      |
| Static Parameters                       |                      |                                                                          |       |      |      |      |
| Drain-Source Breakdown Voltage          | V <sub>(BR)DSS</sub> | V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA                             | 30    | --   | --   | V    |
| Zero Gate Voltage Drain Current         | I <sub>DSS</sub>     | V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V                              | --    | --   | 1    | μA   |
| Gate-Source Leakage                     | I <sub>GSS</sub>     | V <sub>GS</sub> = ±20V                                                   | --    | --   | ±100 | nA   |
| Gate-Source Threshold Voltage           | V <sub>GS(th)</sub>  | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA               | 1.0   |      | 3.0  | V    |
| Drain-Source On-Resistance              | R <sub>DS(on)</sub>  | V <sub>GS</sub> = 10V, I <sub>D</sub> = 10A                              | --    |      | 4    | mΩ   |
|                                         |                      | V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 10A                             | --    |      | 7    |      |
| Forward Transconductance                | g <sub>FS</sub>      | V <sub>GS</sub> = 5V, I <sub>D</sub> =10A                                | --    | 30   | --   | S    |
| Dynamic Parameters                      |                      |                                                                          |       |      |      |      |
| Input Capacitance                       | C <sub>iss</sub>     | V <sub>GS</sub> = 0V,<br>V <sub>DS</sub> = 15V,<br>f = 1.0MHz            | --    | 1714 | --   | pF   |
| Output Capacitance                      | C <sub>oss</sub>     |                                                                          | --    | 339  | --   |      |
| Reverse Transfer Capacitance            | C <sub>rss</sub>     |                                                                          | --    | 326  | --   |      |
| Total Gate Charge                       | Q <sub>g</sub>       | V <sub>DD</sub> = 15V,<br>I <sub>D</sub> = 10A,<br>V <sub>GS</sub> = 10V | --    | 37   | --   | nC   |
| Gate-Source Charge                      | Q <sub>gs</sub>      |                                                                          | --    | 4.8  | --   |      |
| Gate-Drain Charge                       | Q <sub>gd</sub>      |                                                                          | --    | 11   | --   |      |
| Turn-on Delay Time                      | t <sub>d(on)</sub>   | V <sub>DD</sub> = 15V,<br>I <sub>D</sub> = 10A,<br>R <sub>G</sub> = 3Ω   | --    | 8.6  | --   | ns   |
| Turn-on Rise Time                       | t <sub>r</sub>       |                                                                          | --    | 8.1  | --   |      |
| Turn-off Delay Time                     | t <sub>d(off)</sub>  |                                                                          | --    | 29   | --   |      |
| Turn-off Fall Time                      | t <sub>f</sub>       |                                                                          | --    | 8    | --   |      |
| Drain-Source Body Diode Characteristics |                      |                                                                          |       |      |      |      |
| Continuous Body Diode Current           | I <sub>S</sub>       | T <sub>C</sub> = 25°C                                                    | --    | --   | 18   | A    |
| Body Diode Voltage                      | V <sub>SD</sub>      | T <sub>J</sub> = 25°C, I <sub>SD</sub> = 10A, V <sub>GS</sub> = 0V       | --    | --   | 1.2  | V    |
| Reverse Recovery Charge                 | Q <sub>rr</sub>      | I <sub>F</sub> = 10A, V <sub>GS</sub> = 0V<br>di/dt=500A/us              | --    | 40   | --   | nC   |
| Reverse Recovery Time                   | T <sub>rr</sub>      |                                                                          | --    | 14   | --   | ns   |

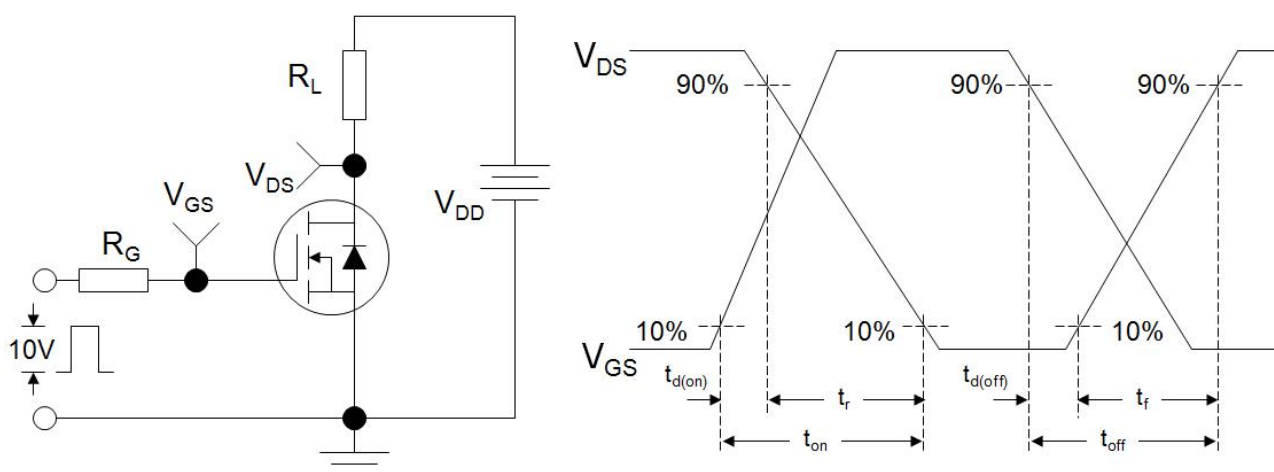
**Notes**

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. EAS condition :  $T_J = 25^{\circ}\text{C}$ ,  $V_{DD} = 30V$ ,  $V_{GS} = 10V$ ,  $L = 0.5mH$ ,  $R_G = 25\Omega$
3. Identical low side and high side switch with identical  $R_G$

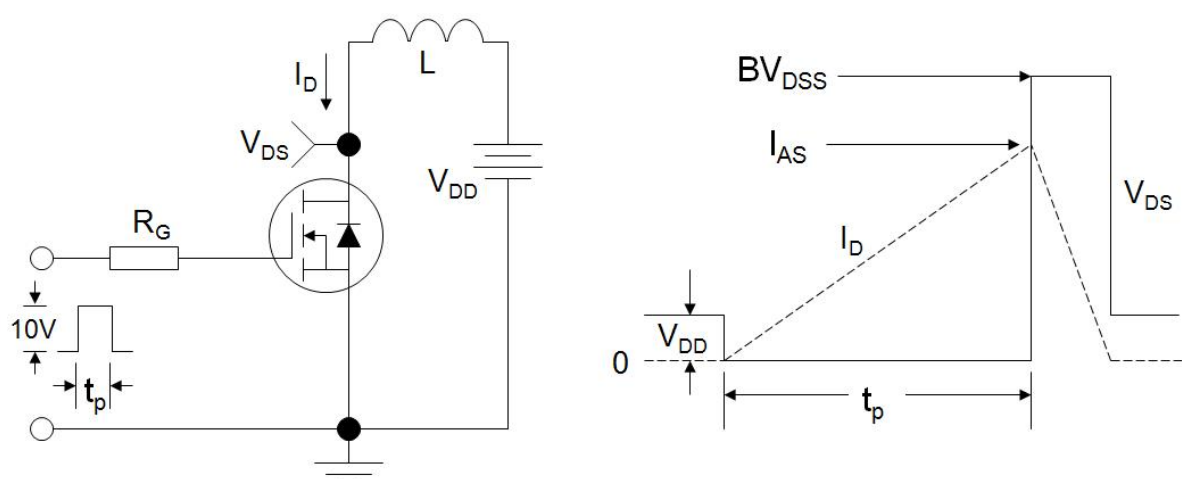
### Gate Charge Test Circuit



### Switch Time Test Circuit



### EAS Test Circuit

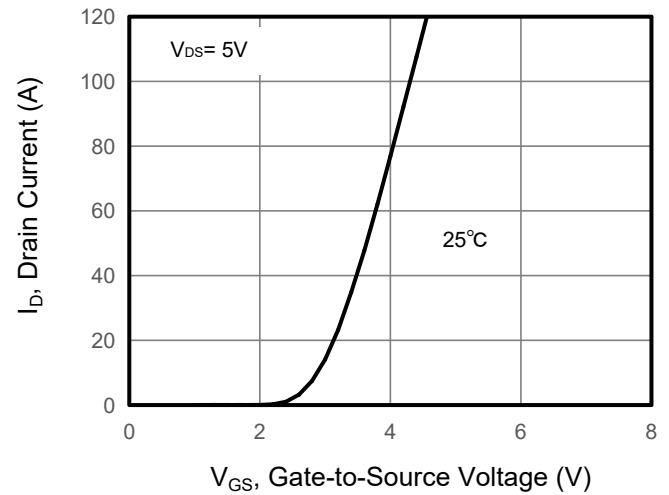


**Typical Characteristics**  $T_J = 25^\circ\text{C}$ , unless otherwise noted

**Figure 1. Output Characteristics**



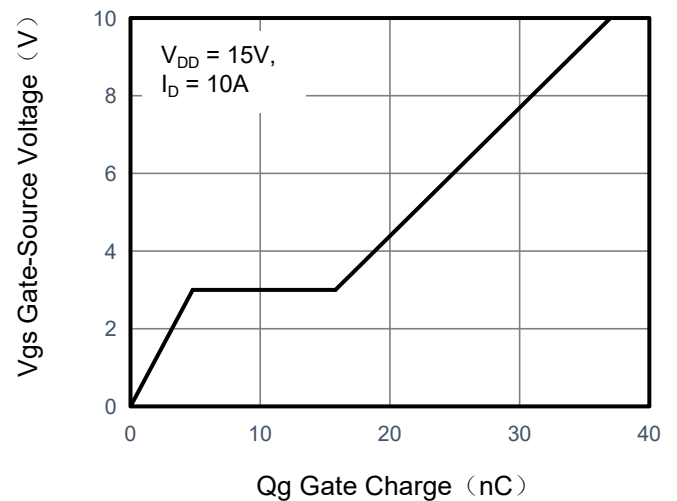
**Figure 2. Transfer Characteristics**



**Figure 3. Drain Source On Resistance**



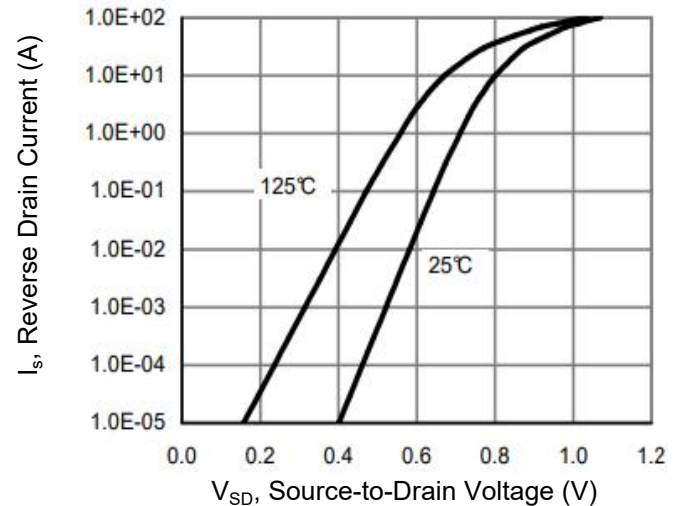
**Figure 4. Gate Charge**



**Figure 5. Capacitance**

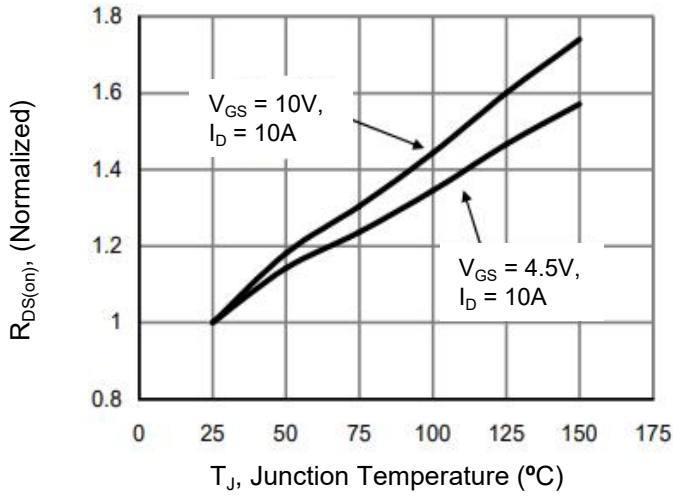


**Figure 6. Source-Drain Diode Forward**

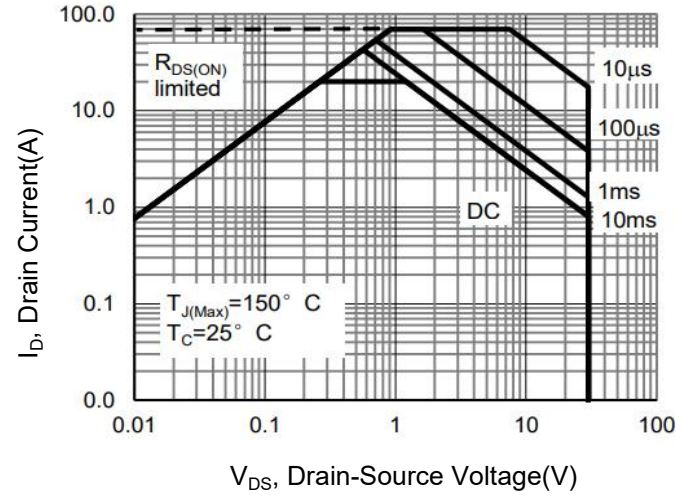


**Typical Characteristics**  $T_J = 25^\circ\text{C}$ , unless otherwise noted

**Figure 7. Drain-Source On-Resistance**



**Figure 8. Safe Operation Area**



**Figure 9. Normalized Maximum Transient Thermal Impedance**

